ABSTRACT

A semiconductor device includes a lower structure, a first interlayer dielectric (ILD) on the lower structure, first pattern regions extending inside the first ILD in a first direction, the first pattern regions being spaced apart from each other in a second direction perpendicular to the first direction, each of the first pattern regions including at least one first pattern, and both ends of the at least one first pattern in the first direction being concave, and second pattern regions extending inside the first ILD in the first direction, the second pattern regions being spaced apart from each other in the second direction and alternating with the first pattern regions in the second direction, and each of the second pattern regions including at least one second pattern.

FIG. 1